TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

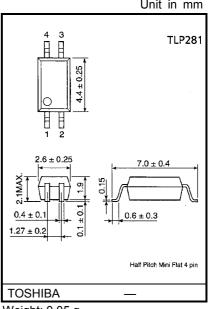
TLP281,TLP281-4

PROGRAMMABLE CONTROLLERS AC/DC-INPUT MODULE PC CARD MODEM(PCMCIA)

TLP281 and TLP281-4 is a very small and thin coupler, suitable for surface mount assembly in applications such as PCMCIA Fax modem,programmable controllers.

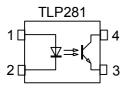
TLP281 and TLP281-4 consist of photo transistor, optically coupled to a gallium arsenide infrared emitting diode.

- Collector-Emitter Voltage : 80 V (MIN)
- Current Transfer Ratio : 50% (MIN) Rank GB
- Isolation Voltage
- UL Recognized •
 - **BSI** Approved
- : 100% (MIN) : 2500 Vrms (MIN) : UL1577, File No. E67349 : BS EN 60065: 1994, : BS EN 41003: 1997
- Certificate No. 8143, 8144

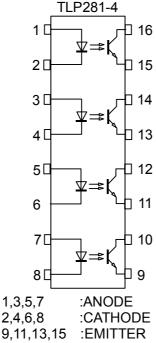


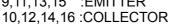
Weight: 0.05 g

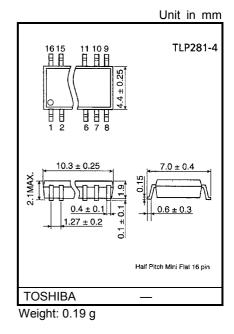
PIN CONFIGURATION(Top view)



1:ANODE 2:CATHODE **3:EMITTER** 4:COLLECTOR







Unit in mm

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RAT	UNIT		
	CHARACTERISTIC	STINBUL	TLP281	TLP281-4	UNIT	
LED	Forward Current	١ _F	5	0	mA	
	Forward Current Derating	∆l _F /°C	−0.7 (Ta≥53°C)	−0.5 (Ta≥25°C)	mA /°C	
	Pulse Forward Current	I _{FP}	1		А	
	Reverse Voltage	V _R	5		V	
	Junction Temperature	Тj	125		°C	
	Collector-Emitter Voltage	V _{CEO}	8	V		
	Emitter-Collector Voltage	V _{ECO}	7		V	
OR	Collector Current	Ι _C	50		mA	
DETECTOR	Collector Power Dissipation (1 Circuit)	P _C	150	100	mW	
Ð	Collector Power Dissipation Derating(Ta≥25°C) (1 Circuit)	∆P _C /°C	-1.5	-1.0	mW /°C	
	Junction Temperature	Tj	125		°C	
Operating Temperature Range		T _{opr}	-55-	°C		
Stor	age Temperature Range	T _{stg}	-55~125		°C	
Lead Soldering Temperature		T _{sol}	260 (10s)		°C	
Total Package Power Dissipation (1 Circuit)		PT	200	170	mW	
Total Package Power Dissipation Derating (Ta≥25°C) (1 Circuit)		∆P _T /°C	-2.0	-1.7	mW /°C	
Isolation Voltage (Note1)		BVS	2500(AC,1min,R.H.≤60%)		Vrms	

(Note1)Device considered a two terminal device : LED side pins shorted together and DETECTOR side pins shorted together.

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

	CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V _F	I _F = 10 mA	1.0	1.15	1.3	V
	Reverse Current	I _R	V _R = 5 V	_	_	10	μA
	Capacitance	CT	V = 0, f = 1 MHz	_	30	_	pF
DETECTOR	Collector-Emitter Breakdown Voltage	V _(BR) CEO	I _C = 0.5 mA	80	_	_	V
	Emitter-Collector Breakdown Voltage	V _(BR) ECO	I _E = 0.1 mA	7	_	_	V
	Collector Dark Current (Note2)	1050	V _{CE} = 48 V, Ambient Light Below (100 <i>t</i> x)		0.01 (2)	0.1 (10)	μA
		'CEO	V _{CE} = 48 V, Ta = 85°C Ambient Light Below (100 ℓx)	_	2 (4)	50 (50)	μA
	Capacitance (Collector to Emitter)	C _{CE}	V = 0, f = 1 MHz	_	10	_	pF

(Note 2) Because of the construction,leak current might be increased by ambient light. Please use photocoupler with less ambient light.

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I _C / I _F	I _F = 5 mA, V _{CE} = 5 V	50	_	600	%
		Rank GB	100	_	600	70
Saturated CTR	I _C / I _{F (sat)}	IF = 1 mA, VCE = 0.4 V	_	60	_	%
		Rank GB	30	_	_	/0
Collector-Emitter		I _C = 2.4 mA, I _F = 8 mA	_	_	0.4	
Saturation Voltage	V _{CE (sat)}	I _C = 0.2 mA, I _F = 1 mA	_	0.2	_	V
Saturation Voltage		Rank GB	_	_	0.4	
Off-State Collector Current	I _{C (off)}	V _F = 0.7 V, V _{CE} = 48 V	_	_	10	μA

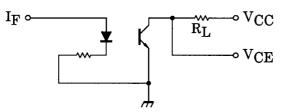
ISOLATION CHARACTERISTICS (Ta = 25°C)

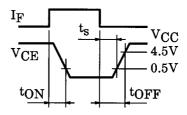
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	CS	V _S = 0 V, f = 1 MHz	_	0.8	_	pF
Isolation Resistance	R _S	V _S = 500 V, R.H.≤60%	5×10 ¹⁰	10 ¹⁴	_	Ω
	BVS	AC , 1 minute	2500		_	Vrms
Isolation Voltage		AC , 1 second,in OIL	_	5000	_	
		DC , 1 minute, in OIL	_	5000		Vdc

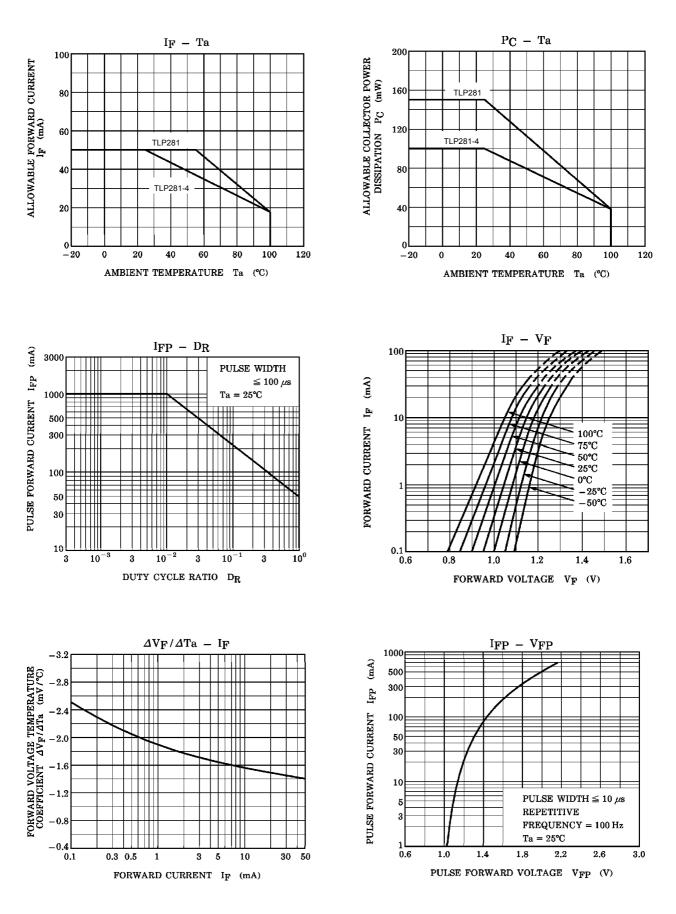
SWITCHING CHARACTERISTICS (Ta = 25°C)

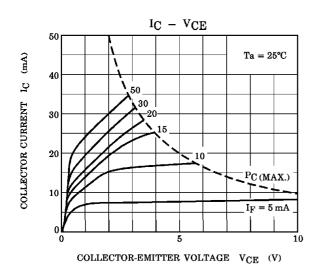
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	tr	V _{CC} = 10 V, I _C = 2 mA R _L = 100Ω	_	2	_	
Fall Time	t _f			3	_	μs
Turn-On Time	t _{on}			3	_	
Turn-Off Time	t _{off}		_	3	—	
Turn-On Time	t _{ON}	R _L = 1.9 kΩ (Fig.1) V _{CC} = 5 V, I _F = 16 mA		2	_	
Storage Time	ts			25	_	μs
Turn-Off Time	tOFF		_	40	_	

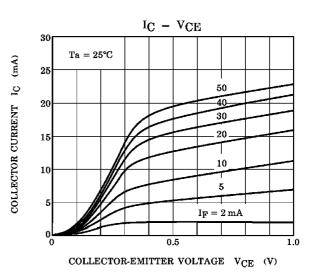
(Fig.1)SWITCHING TIME TEST CIRCUIT

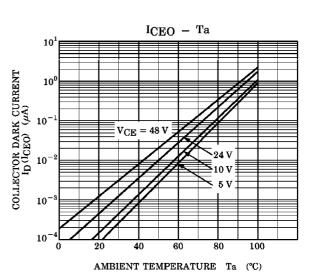


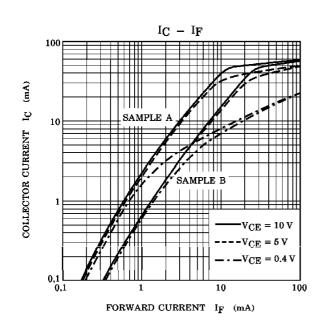


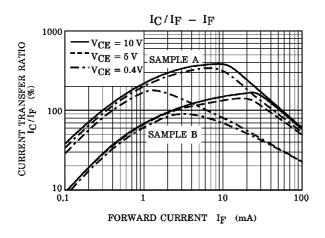


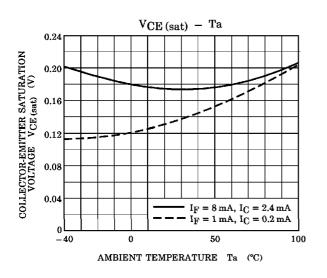


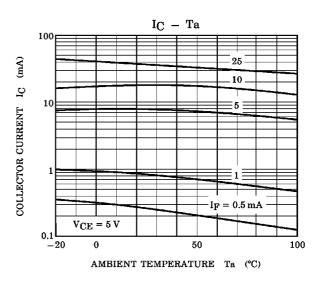


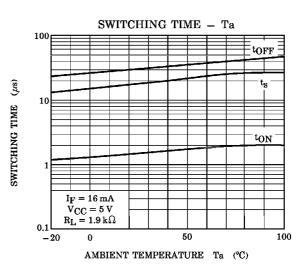












SWITCHING TIME – RL 100 Ta = 25°C IF = 16 mA VCC = 5 V 100 100 100 LOAD RESISTANCE RL (kΩ)

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